Product data sheet

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT82 (SIP3) plastic package intended for use in general purpose bidirectional switching and phase control applications. This "series E" sensitive gate triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- · High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Low holding current for low current loads and lowest EMI at commutation
- · Triggering in all four quadrants
- Compact package
- · Direct interfacing to logic level ICs
- · Direct interfacing to low power gate drive circuits
- Sensitive gate

3. Applications

- General purpose low power motor control
- Home appliances
- · Industrial process control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values		Unit			
Absolute maximum rating								
V_{DRM}	repetitive peak off-state voltage			8	00		V	
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	4 A			А		
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	25 A			А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static ch	aracteristics			,				
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$		-	2.5	10	mA	
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;} $ $T_j = 25 \text{ °C; } Fig. 7$		-	4	10	mA	
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	5	10	mA	
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	11	25	mA	
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; Fig. 9$		-	2.2	15	mA	

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	·/	
2	T2	main terminal 2		Ν
3	G	gate		T2 — T1
mb	T2	mounting base; main terminal 2	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	Sym051
			()()()	
			□ □ □ 1 2 3	

6. Ordering information

Table 3. Ordering information

Type number	Package	kage				
	Name	Description	Version			
BT134-800E	SIP3	plastic single-ended package; 3-leads (in-line)	SOT82			

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT134-800E	BT134-800E

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; <u>Fig 1</u> ; <u>Fig 2</u> ; <u>Fig 3</u>	4	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig 4; Fig 5	25	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	27	А
l ² t	I ² t for fusing	t _P = 10 ms; SIN	3.1	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 20 mA; T2+ G+	50	A/µs
		I _G = 20 mA; T2+ G-	50	A/µs
		I _G = 20 mA; T2- G-	50	A/µs
		I _G = 50 mA; T2- G+	10	A/µs
I _{GM}	peak gate current		2	А
P_GM	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		125	°C

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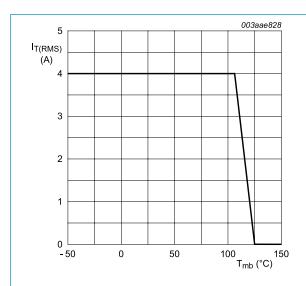
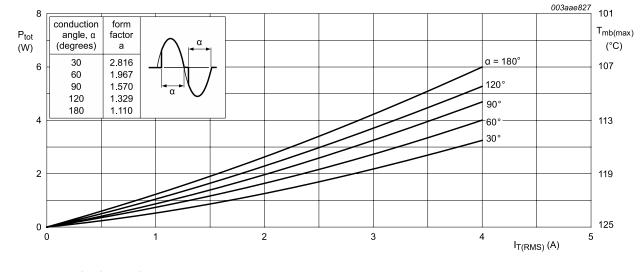


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

f = 50 Hz; T_{mb} ≤ 107 °C Fig. 2. RMS on-state current as a function of surge duration; maximum values



α = conduction angle

 $a = form factor = I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

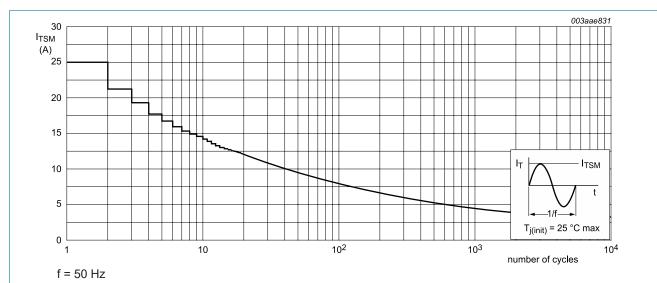
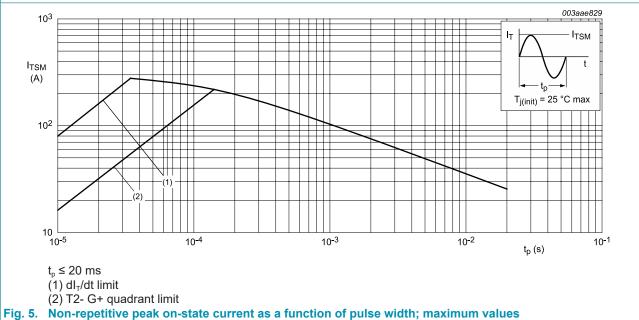


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	half cycle; Fig 6	-	-	3.7	K/W
from junction to mounting base	_	full cycle; Fig 6	-	-	3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	100	-	K/W

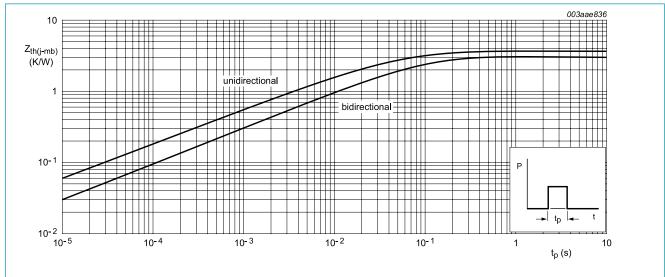


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

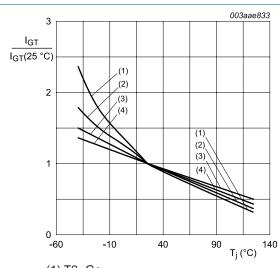
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	-	4	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 7}$	-	11	25	mA
l _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	3	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	10	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	2.5	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	4	20	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	2.2	15	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	$V_D = 800 \text{ V}; I_{TM} = 6 \text{ A}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

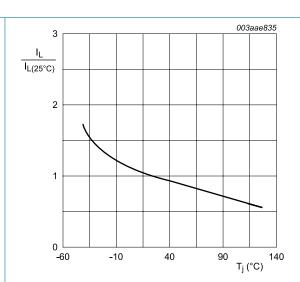


Fig. 8. Normalized latching current as a function of junction temperature

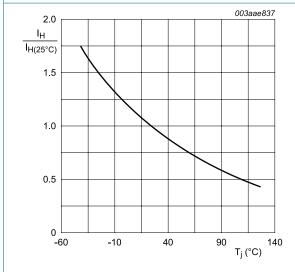
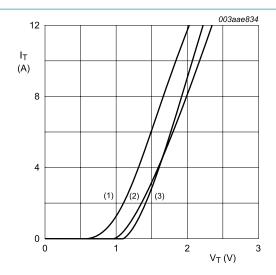


Fig. 9. Normalized holding current as a function of junction temperature



 $V_o = 1.27 \text{ V}; R_s = 0.091 \Omega$

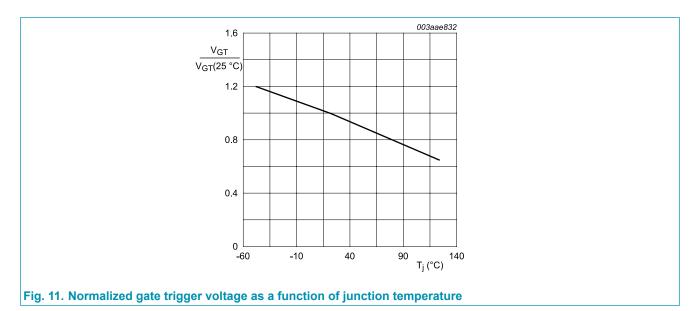
(1) T_i = 125 °C; typical values

(2) T_i = 125 °C; maximum values

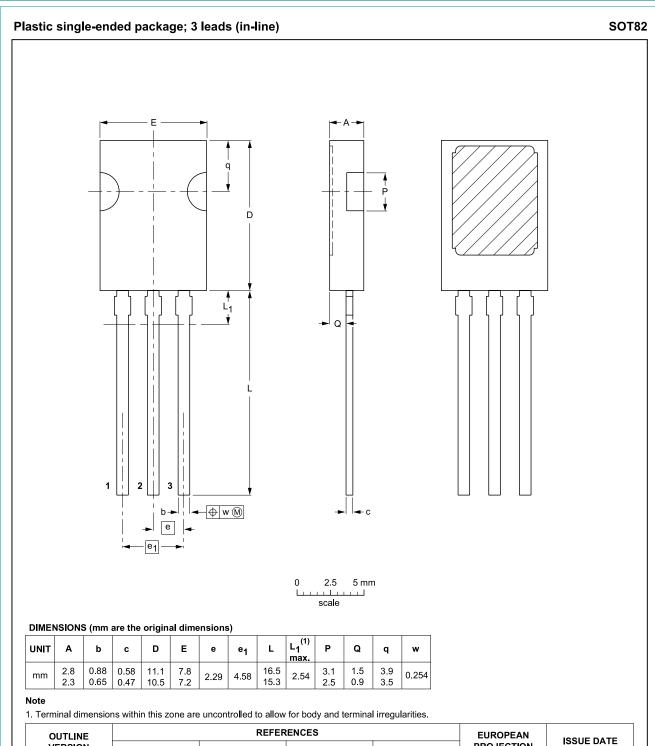
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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11. Package outline



OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	ElAJ		PROJECTION	ISSUE DATE
SOT82						97-06-11

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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